

MITSUBISHI IGBT MODULES
CM600DY-12NF

HIGH POWER SWITCHING USE

CM600DY-12NF



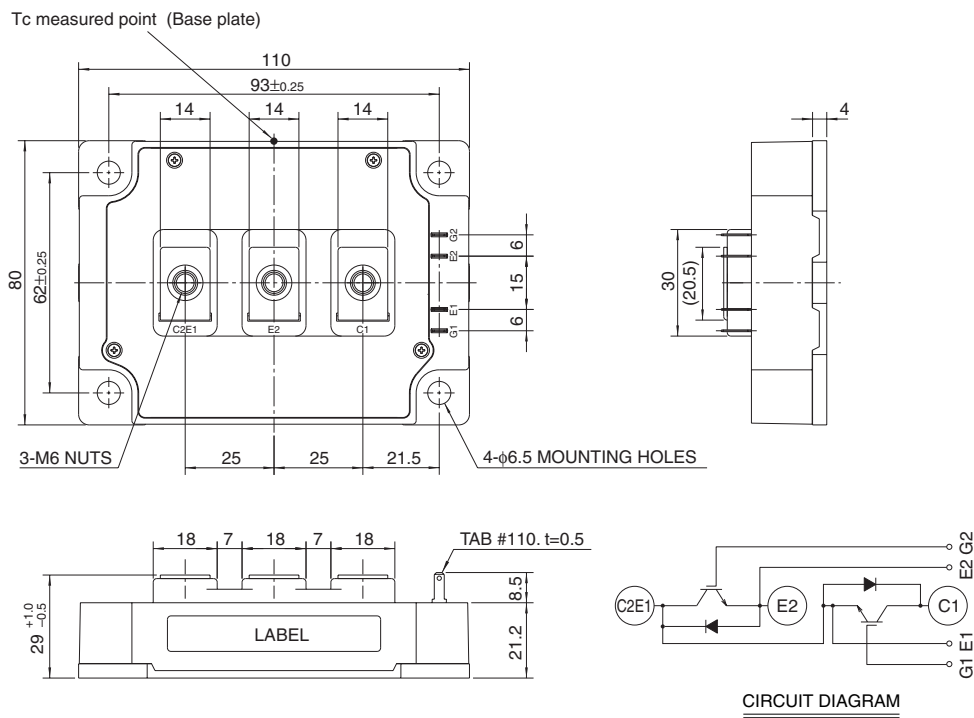
- IC 600A
- VCES 600V
- Insulated Type
- 2-elements in a pack

APPLICATION

General purpose inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS (T_j = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	DC, T _c ' = 89°C ^{*3}	600	A
I _{CM}		Pulse (Note 2)	1200	A
I _E (Note 1)	Emitter current		600	A
I _{EM} (Note 1)		Pulse (Note 2)	1200	A
P _C (Note 3)	Maximum collector dissipation	T _c = 25°C	1130	W
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
V _{iso}	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	Vrms
—	Torque strength	Main terminals M6 screw	3.5 ~ 4.5	N • m
—		Mounting M6 screw	3.5 ~ 4.5	N • m
—	Weight	Typical value	580	g

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	—	—	1	mA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C = 60mA, V _{CE} = 10V	5	6	7.5	V	
I _{GES}	Gate leakage current	±V _{GE} = V _{GES} , V _{CE} = 0V	—	—	0.5	µA	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 600A, V _{GE} = 15V	T _j = 25°C	—	1.7	2.2	V
			T _j = 125°C	—	1.7	—	
C _{ies}	Input capacitance	V _{CE} = 10V V _{GE} = 0V	—	—	90	nF	
C _{oes}	Output capacitance		—	—	11	nF	
C _{res}	Reverse transfer capacitance		—	—	3.6	nF	
Q _G	Total gate charge	V _{CC} = 300V, I _C = 600A, V _{GE} = 15V	—	2400	—	nC	
t _{d(on)}	Turn-on delay time	V _{CC} = 300V, I _C = 600A V _{GE} = ±15V R _G = 1Ω, Inductive load I _E = 600A	—	—	500	ns	
t _r	Turn-on rise time		—	—	300	ns	
t _{d(off)}	Turn-off delay time		—	—	750	ns	
t _f	Turn-off fall time		—	—	300	ns	
t _{rr} (Note 1)	Reverse recovery time		—	—	250	ns	
Q _{rr} (Note 1)	Reverse recovery charge	—	8.7	—	µC		
V _{EC} (Note 1)	Emitter-collector voltage	I _E = 600A, V _{GE} = 0V	—	—	2.6	V	
R _{th(j-c)Q}	Thermal resistance ^{*1}	IGBT part (1/2 module)	—	—	0.11	K/W	
R _{th(j-c)R}		FWDi part (1/2 module)	—	—	0.18	K/W	
R _{th(c-f)}	Contact thermal resistance	Case to heat sink, Thermal compound Applied ^{*2} (1/2 module)	—	0.02	—	K/W	
R _{th(j-c')Q}	Thermal resistance	Case temperature measured point is just under the chips	—	—	0.046 ^{*3}	K/W	
R _G	External gate resistance		1.0	—	10	Ω	

*1 : Case temperature (T_c) measured point is shown in page OUTLINE DRAWING.

*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

*3 : Case temperature (T_c) measured point is just under the chips.

If you use this value, R_{th(f-a)} should be measured just under the chips.

Note 1. I_E, V_{EC}, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.